

## PSMN2R7-30PL

# N-channel 30 V 2.7 m $\Omega$ logic level MOSFET in TO-220 Rev. 02 — 2 November 2010 Product

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Logic level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol               | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|----------------------|--|---|-----|-----|-----|-----|------|
| $V_{DS}$             | drain-source voltage                               | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$   |     | -   | -   | 30  | V    |
| I <sub>D</sub>       | drain current                                      | $T_{mb}$ = 25 °C; $V_{GS}$ = 10 V;<br>see <u>Figure 1</u>   | [1] | -   | -   | 100 | Α    |
| P <sub>tot</sub>     | total power dissipation                            | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>  |     | -   | -   | 170 | W    |
| T <sub>j</sub>       | junction temperature                               |   |     | -55 | -   | 175 | °C   |
| Static chara         | acteristics  |   |     |     |     |     |      |
| R <sub>DSon</sub>    | drain-source on-state resistance                   | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$  | [2] | -   | 2.2 | 2.7 | mΩ   |
| Dynamic ch           | naracteristics                                     |   |     |     |     |     |      |
| $Q_{GD}$             | gate-drain charge                                  | $V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$   |     | -   | 8   | -   | nC   |
| Q <sub>G(tot)</sub>  | total gate charge                                  | V <sub>DS</sub> = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>   |     | -   | 32  | -   | nC   |
| Avalanche ruggedness |  |   |     |     |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive<br>drain-source avalanche<br>energy | $\begin{split} &V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C;} \\ &I_D = 100 \text{ A; } V_{sup} \leq 30 \text{ V;} \\ &R_{GS} = 50  \Omega; \text{ unclamped} \end{split}$ |     | -   | -   | 300 | mJ   |

<sup>[1]</sup> Continuous current is limited by package.



<sup>[2]</sup> Measured 3 mm from package.

### 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1   | G      | gate                              |                    | _              |
| 2   | D      | drain                             | mb                 | D              |
| 3   | S      | source                            |                    | $\mathbf{G}$   |
| mb  | D      | mounting base; connected to drain | 1 2 3              | mbb076 S       |
|     |        |                                   | SOT78 (TO-220AB)   |                |

### 3. Ordering information

Table 3. Ordering information

| Type number  | Package  |  |         |
|--------------|----------|--|---------|
|              | Name     | Description  | Version |
| PSMN2R7-30PL | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |

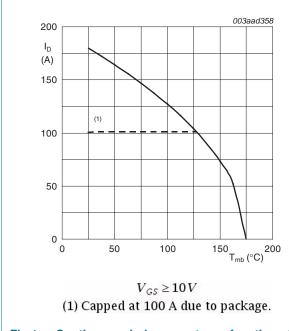
### 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

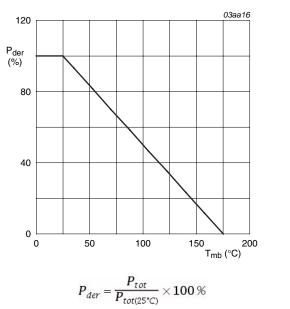
|                      |  | · · · · · · · · · · · · · · · · · · ·   |            |     |     |      |
|----------------------|--|---|------------|-----|-----|------|
| Symbol               | Parameter                                    | Conditions  |            | Min | Max | Unit |
| $V_{DS}$             | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C   |            | -   | 30  | V    |
| $V_{DGR}$            | drain-gate voltage                           | $T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ   |            | -   | 30  | V    |
| $V_{GS}$             | gate-source voltage                          |   |            | -20 | 20  | V    |
| I <sub>D</sub>       | drain current                                | $V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$           | <u>[1]</u> | -   | 100 | Α    |
|                      |  | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>  | [1]        | -   | 100 | Α    |
| I <sub>DM</sub>      | peak drain current                           | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3  |            | -   | 730 | Α    |
| P <sub>tot</sub>     | total power dissipation                      | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>  |            | -   | 170 | W    |
| T <sub>stg</sub>     | storage temperature                          |   |            | -55 | 175 | °C   |
| Tj                   | junction temperature                         |   |            | -55 | 175 | °C   |
| Source-drain         | diode  |   |            |     |     |      |
| I <sub>S</sub>       | source current                               | T <sub>mb</sub> = 25 °C   | <u>[1]</u> | -   | 100 | Α    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$  |            | -   | 730 | Α    |
| Avalanche rug        | ggedness                                     |   |            |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 $\Omega$ ; unclamped |            | -   | 300 | mJ   |

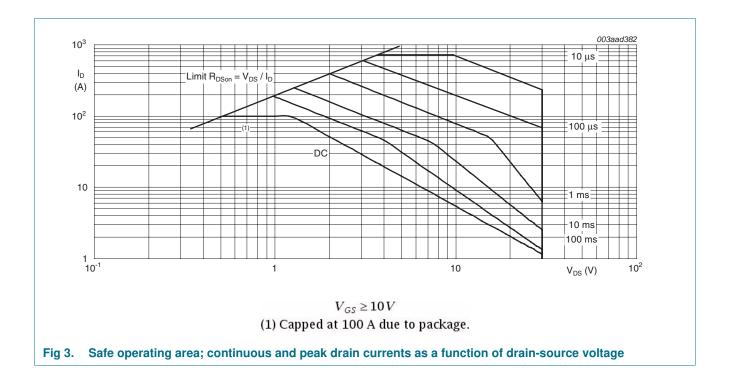
[1] Continuous current is limited by package.



Continuous drain current as a function of mounting base temperature

Fig 2. Normalized total power dissipation as a function of mounting base temperature





### 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter   | Conditions   | Min | Тур  | Max  | Unit |
|----------------|---|--------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 4 | -   | 0.54 | 0.88 | K/W  |

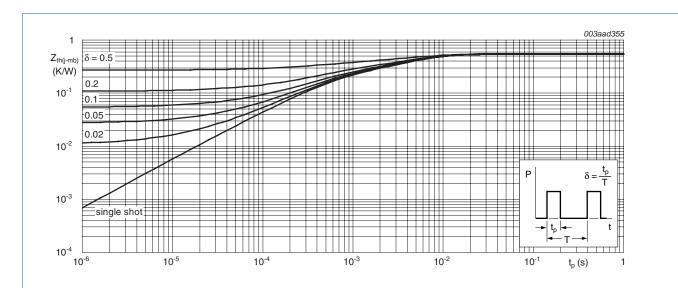


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

### 6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

| Symbol   | Parameter                         | Conditions  | Min   | Тур  | Max  | Unit |
|--|-----------------------------------|---|-------|------|------|------|
| Static chara                                       | acteristics                       |   |       |      |      |      |
| V <sub>(BR)DSS</sub>                               | drain-source breakdown            | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$  | 30    | -    | -    | V    |
|  | voltage                           | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$   | 27    | -    | -    | V    |
| V <sub>GS(th)</sub>                                | gate-source threshold voltage     | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C;<br>see <u>Figure 10</u> ; see <u>Figure 11</u>         | 1.3   | 1.7  | 2.15 | V    |
|  |                                   | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 11   | 0.5   | -    | -    | V    |
|  |                                   | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 11   | -     | -    | 2.45 | V    |
| I <sub>DSS</sub>                                   | drain leakage current             | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                      | -     | 0.3  | 5    | μΑ   |
|  |                                   | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 ^{\circ}\text{C}$                               | -     | -    | 100  | μΑ   |
| I <sub>GSS</sub>                                   | gate leakage current              | $V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                      | -     | 10   | 100  | nΑ   |
|  |                                   | $V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                     | -     | 10   | 100  | nΑ   |
| R <sub>DSon</sub> drain-source on-state resistance |                                   | $V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12                        | -     | 2.7  | 3.6  | mΩ   |
|  |                                   | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$<br>see Figure 13                     | -     | -    | 5.13 | mΩ   |
|  |                                   | $V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$<br>see <u>Figure 13</u>             | -     | -    | 6.84 | mΩ   |
|  |                                   | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$<br>see Figure 13                     | -     | -    | 3.5  | mΩ   |
|  |                                   | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$<br>see Figure 12                      | [1] - | 2.2  | 2.7  | mΩ   |
| $R_G$  | gate resistance                   | f = 1 MHz   | -     | 1    | -    | Ω    |
| Dynamic ch   | naracteristics                    |   |       |      |      |      |
| $Q_{G(tot)}$                                       | total gate charge                 | $I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15 | -     | 66   | -    | nC   |
|  |                                   | $I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$  | -     | 60   | -    | nC   |
|  |                                   | $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$                                    | -     | 32   | -    | nC   |
| Q <sub>GS</sub>                                    | gate-source charge                | see <u>Figure 14</u> ; see <u>Figure 15</u>   | -     | 12   | -    | nC   |
| Q <sub>GS(th)</sub>                                | pre-threshold gate-source charge  |   | -     | 6.4  | -    | nC   |
| Q <sub>GS(th-pl)</sub>                             | post-threshold gate-source charge |   | -     | 5.6  | -    | nC   |
| Q <sub>GD</sub>                                    | gate-drain charge                 |   | -     | 8    | -    | nC   |
| V <sub>GS(pl)</sub>                                | gate-source plateau voltage       | V <sub>DS</sub> = 15 V  | -     | 2.6  | -    | ٧    |
| C <sub>iss</sub>                                   | input capacitance                 | $V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$                                       | -     | 3954 | -    | pF   |
| C <sub>oss</sub>                                   | output capacitance                | T <sub>j</sub> = 25 °C; see <u>Figure 16</u>  | -     | 822  | -    | pF   |
| C <sub>rss</sub>                                   | reverse transfer capacitance      |   | -     | 356  | -    | pF   |

 Table 6.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

| Symbol              | Parameter             | Conditions  | Min | Тур | Max | Unit |
|---------------------|-----------------------|---|-----|-----|-----|------|
| t <sub>d(on)</sub>  | turn-on delay time    | $V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$                    | -   | 46  | -   | ns   |
| t <sub>r</sub>      | rise time             | $R_{G(ext)} = 4.7 \Omega$   | -   | 82  | -   | ns   |
| t <sub>d(off)</sub> | turn-off delay time   |   | -   | 74  | -   | ns   |
| t <sub>f</sub>      | fall time             |   | -   | 35  | -   | ns   |
| Source-dra          | in diode              |   |     |     |     |      |
| $V_{SD}$            | source-drain voltage  | $I_S = 15 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17 | -   | 0.7 | 1.2 | V    |
| t <sub>rr</sub>     | reverse recovery time | $I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$                           | -   | 40  | -   | ns   |
| Q <sub>r</sub>      | recovered charge      | $V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}$   | -   | 33  | -   | nC   |

### [1] Measured 3 mm from package.

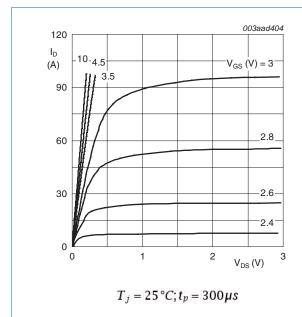


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

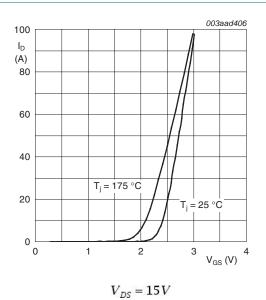


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

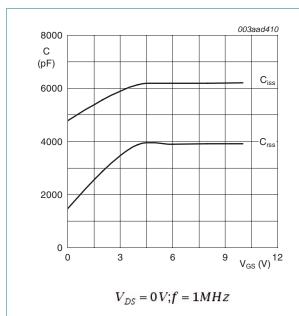


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

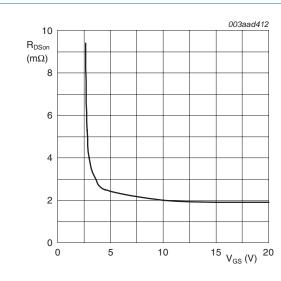
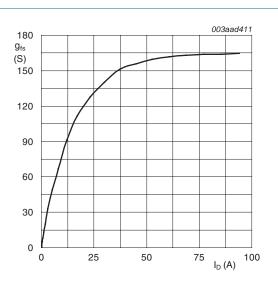


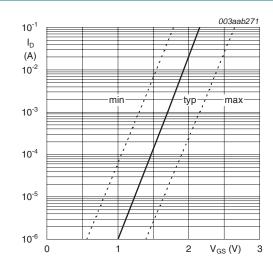
Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25 \,^{\circ}C; I_D = 25A$ 



 $T_j = 25\,^{\circ}C; V_{DS} = 15\,V$ 

Fig 8. Forward transconductance as a function of drain current; typical values



$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

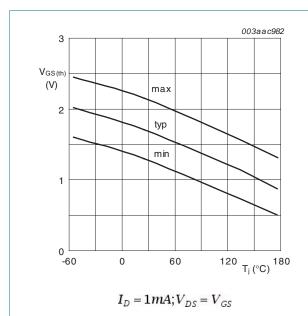


Fig 11. Gate-source threshold voltage as a function of junction temperature

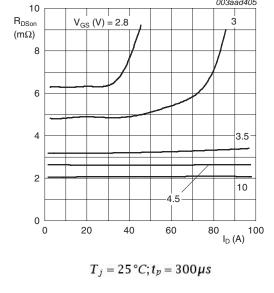


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

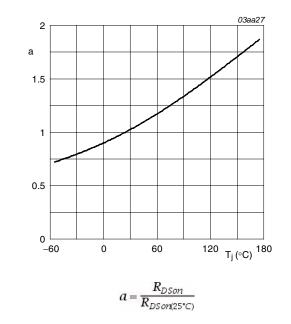


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

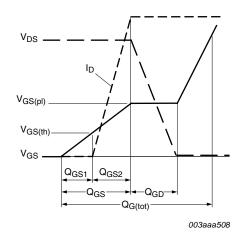


Fig 14. Gate charge waveform definitions

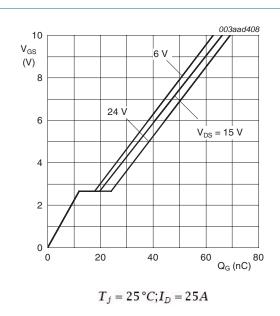
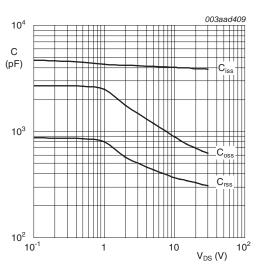


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

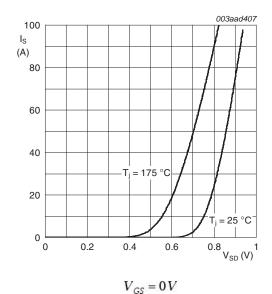
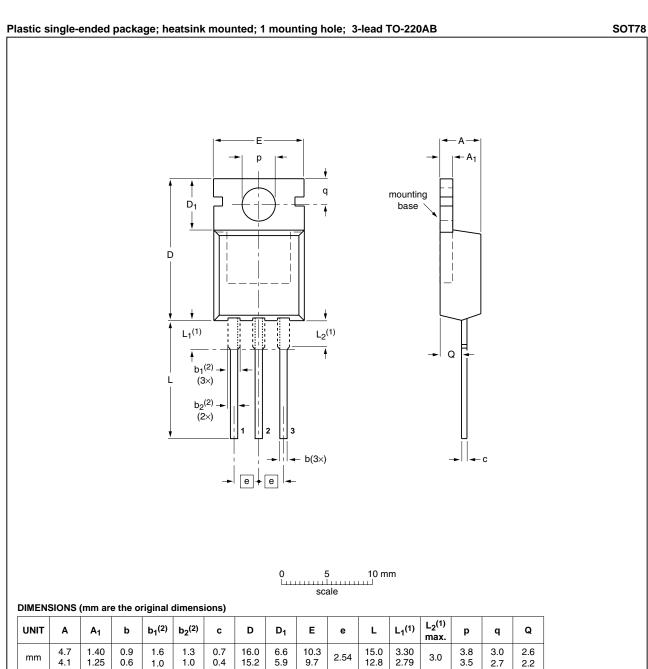


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

### Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

| OUTLINE |     | REFER           | ENCES | EUROPEAN   | ISSUE DATE                      |
|---------|-----|-----------------|-------|------------|---------------------------------|
| VERSION | IEC | JEDEC           | JEITA | PROJECTION | ISSUE DATE                      |
| SOT78   |     | 3-lead TO-220AB | SC-46 |            | <del>08-04-23</del><br>08-06-13 |

Fig 18. Package outline SOT78 (TO-220AB)

PSMN2R7-30PL

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### 8. Revision history

### Table 7. Revision history

| Document ID      | Release date  | Data sheet status                              | Change notice | Supersedes       |
|------------------|---|--|---------------|------------------|
| PSMN2R7-30PL v.2 | 20101102  | Product data sheet                             | -             | PSMN2R7-30PL v.1 |
| Modifications:   | <ul><li>Status changed</li><li>Various change</li></ul> | d from objective to product.<br>es to content. |               |                  |
| PSMN2R7-30PL v.1 | 20100226  | Objective data sheet                           | -             | -                |

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#### 9.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

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- [2] The term 'short data sheet' is explained in section "Definitions"
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## PSMN2R7-30PL

### **Nexperia**

N-channel 30 V 2.7 m $\Omega$  logic level MOSFET in TO-220

### 11. Contents

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